

Description

IRF630N, the silicon N-channel Enhanced MOSFETs, is obtained by advanced MOSFET technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor is suitable device for SMPS, high speed switching and general purpose applications.

KEY CHARACTERISTICS

Parameter	Value	Unit
V_{DS}	200	V
I_D	9	A
$R_{DS(ON),Typ}$	0.26	Ω

FEATURES

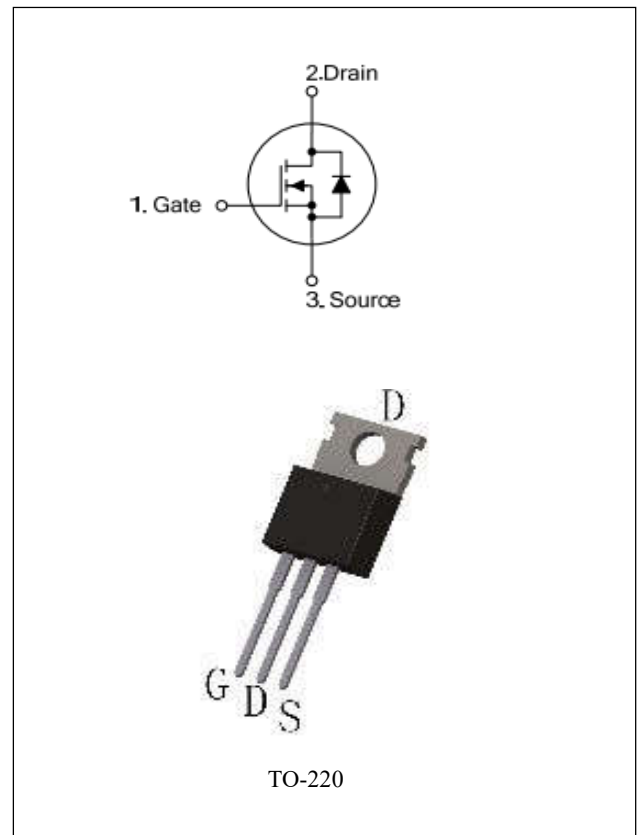
- ① Fast Switching
- ② Low C_{rss}
- ③ 100% avalanche tested
- ④ Improved dv/dt capability
- ⑤ RoHS product

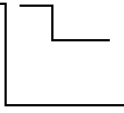
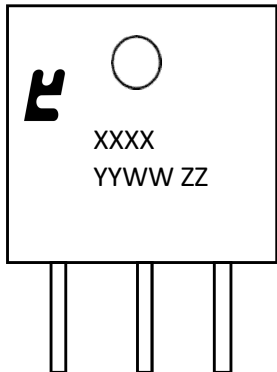
APPLICATIONS

High frequency switching mode power supply

ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
IRF630N	TO-220	IRF630N	Tube



IRF630N  (2) Package type (1) Chip name (1)IRF630N:200V 9A (2) A:TO-220	 XXXX: Product Code YYWW: Year&Week ZZ: Assembly Code
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ABSOLUTE RATINGS

at TC = 25°C, unless otherwise specified

Symbol	Parameter	Rating	Units
V _{DSS}	Drain-to-Source Voltage	200	V
I _D	Continuous Drain Current	9	A
	Continuous Drain Current TC = 100 °C	5.5	A
I _{DM}	Pulsed Drain Current(Note1)	36	A
V _{GS}	Gate-to-Source Voltage	±30	V
E _{AS}	Single Pulse Avalanche Energy(Note2)	200	mJ
d _V /dt	Peak Diode Recovery dv/dt(Note3)	5.0	V/ns
P _D	Power Dissipation TO-220, TO-251, TO-252	75	W
	Derating Factor above 25°C	0.6	W/°C
P _D	Power Dissipation TO-220F	30	W
	Derating Factor above 25°C	0.24	W/°C
T _J , T _{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	°C
T _L	Maximum Temperature for Soldering	300	°C

Thermal characteristics
Thermal characteristics (No FullPAK) TO-220\TO-251\TO-252

Symbol	Parameter	RATINGS	Units
R _{θJC}	Junction-to-Case	1.67	°C/W
R _{θJA}	Junction-to-Ambient	62.5	°C/W

Thermal characteristics (FullPAK) TO-220F

Symbol	Parameter	RATINGS	Units
R _{θJC}	Junction-to-Case	4.17	°C/W
R _{θJA}	Junction-to-Ambient	62.5	°C/W

Electrical Characteristics
at TC = 25°C, unless otherwise specified

OFF Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	200	--	--	V
$\Delta BVDSS/\Delta T_J$	Bvdss Temperature Coefficient	$I_D=250\mu A$, Reference 25°C	--	0.25	--	V/°C
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=200V, V_{GS}=0V$, $T_J=25^\circ C$	--	--	1	μA
		$V_{DS}=160V, V_{GS}=0V$, $T_J=125^\circ C$	--	--	100	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+30V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-30V$	--	--	100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On- Resistance	$V_{GS}=10V, I_D=4A(\text{Note4})$	--	0.26	0.32	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu A(\text{Note4})$	2.0	--	4.0	V

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
R_g	Gate resistance	$f=1.0MHz$	--	3.5	--	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=25V$ $f=1.0MHz$	--	550	--	PF
C_{oss}	Output Capacitance		--	90	--	
C_{rss}	Reverse Transfer Capacitance		--	8.6	--	

Switching Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=9A$ $V_{DD}=100V$ $V_{GS}=10V$ $R_G=5\Omega$	--	10	--	ns
t_r	Rise Time		--	5	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	20	--	
t_f	Fall Time		--	7	--	
Q_g	Total Gate Charge	$I_D=9A$ $V_{DD}=160V$ $V_{GS}=10V$	--	12	--	nC
Q_{gs}	Gate to Source Charge		--	3	--	
Q_{gd}	Gate to Drain ("Miller") Charge		--	6	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)	$T_C=25\text{ }^\circ\text{C}$	--	--	9	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	36	A
V_{SD}	Diode Forward Voltage	$I_S=9A$, $V_{GS}=0V(\text{Note4})$	--	--	1.2	V
T_{rr}	Reverse Recovery Time	$I_S=9A$, $T_J=25\text{ }^\circ\text{C}$ $dI_F/dt=100A/\mu s$	--	110	--	ns
Q_{rr}	Reverse Recovery Charge		--	465	--	nC

Note1: Pulse width limited by maximum junction temperature

Note2: $L=20mH$, $V_{DS}=50V$, Start $T_J=25\text{ }^\circ\text{C}$

Note3: $I_{SD}=9A$, $dI/dt \leq 100A/\mu s$, $V_{DD} \leq BV_{DS}$, Start $T_J=25\text{ }^\circ\text{C}$

Note4: Pulse width $t_p \leq 300\mu s$, $\delta \leq 2\%$

Characteristics Curves

Figure 1a Safe Operating Area (No FullPAK)

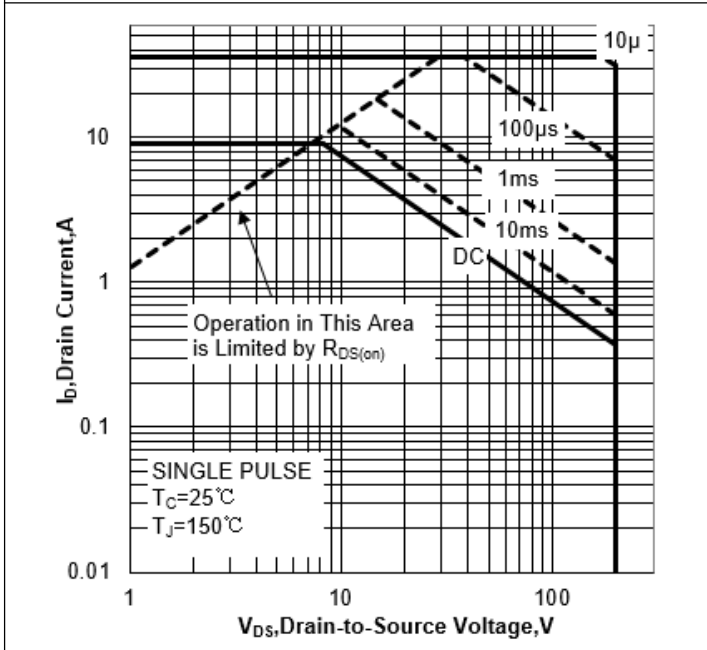


Figure 1b Safe Operating Area (FullPAK)

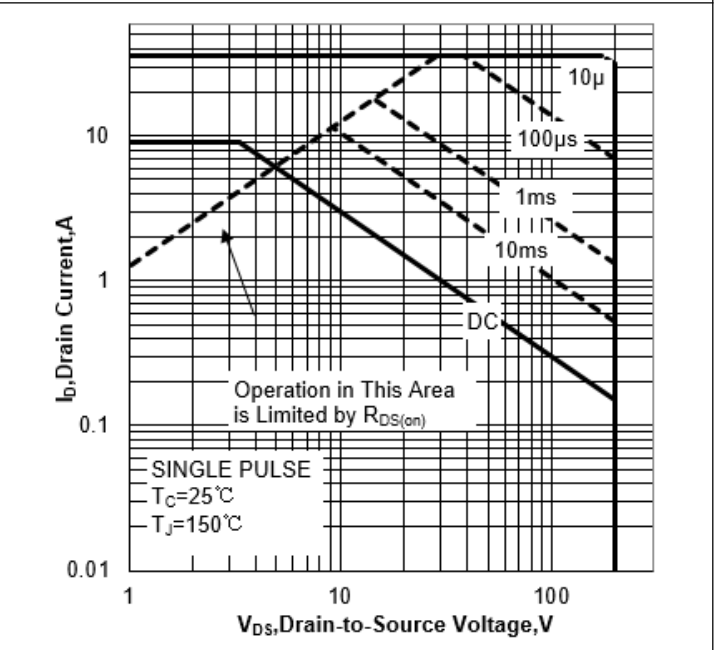


Figure 2a Power Dissipation (No FullPAK)

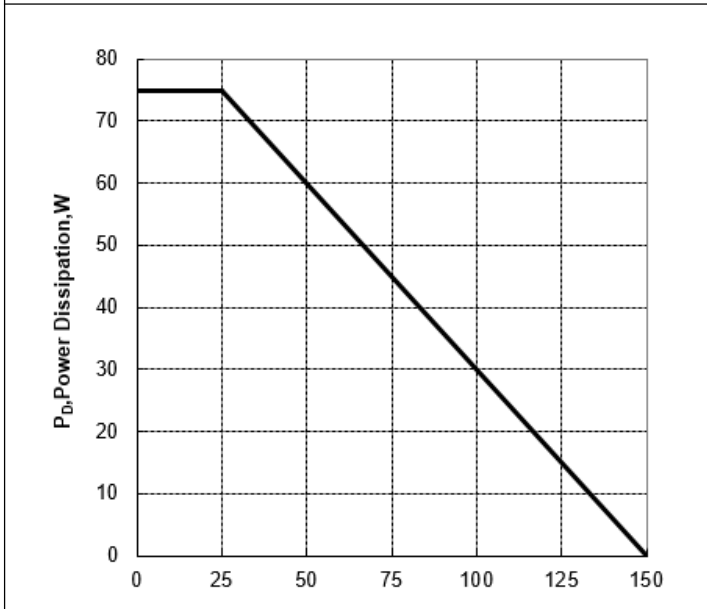


Figure 2b Power Dissipation (FullPAK)

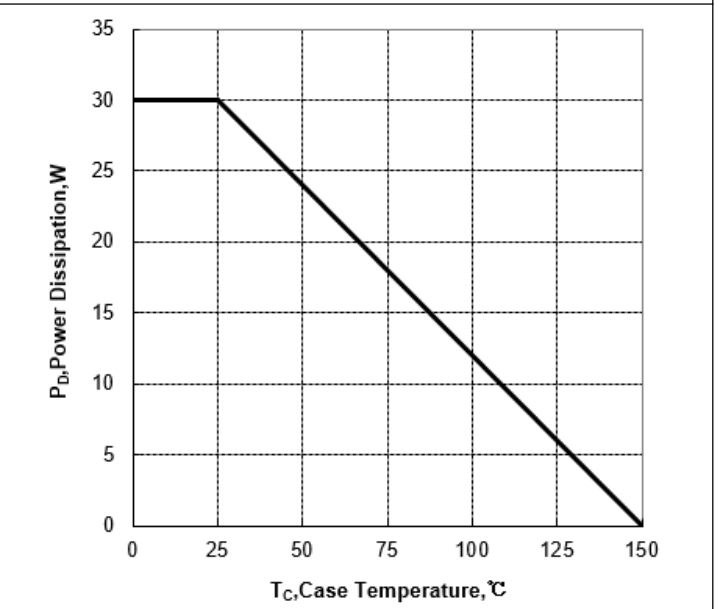


Figure 3a Max Thermal Impedance (No FullPAK)

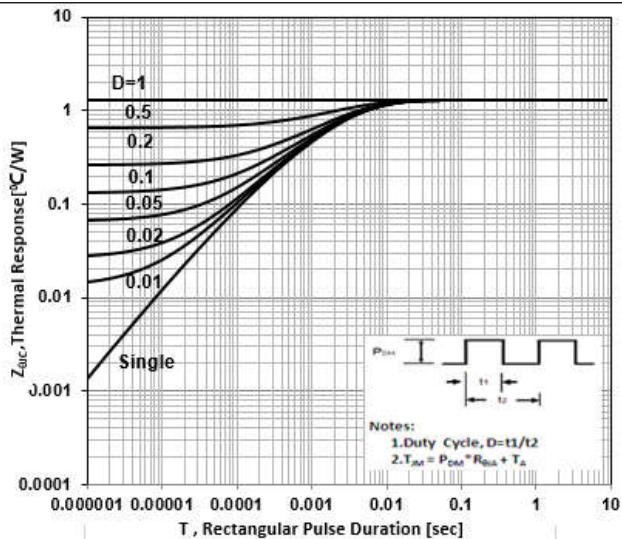


Figure 3b Max Thermal Impedance (FullPAK)

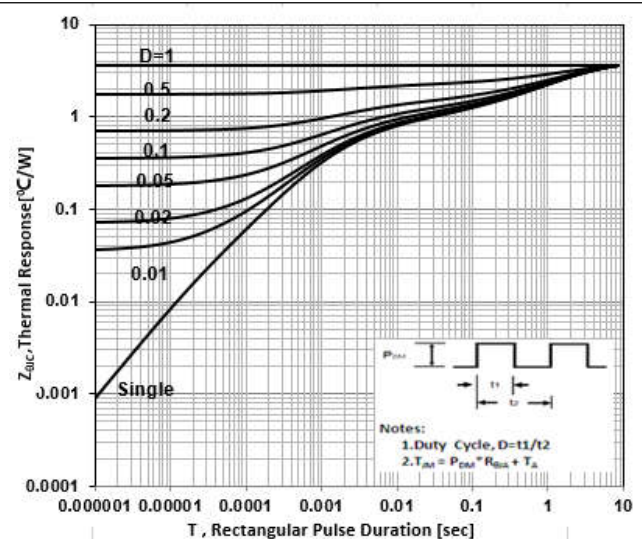


Figure 4 Typical Output Characteristics

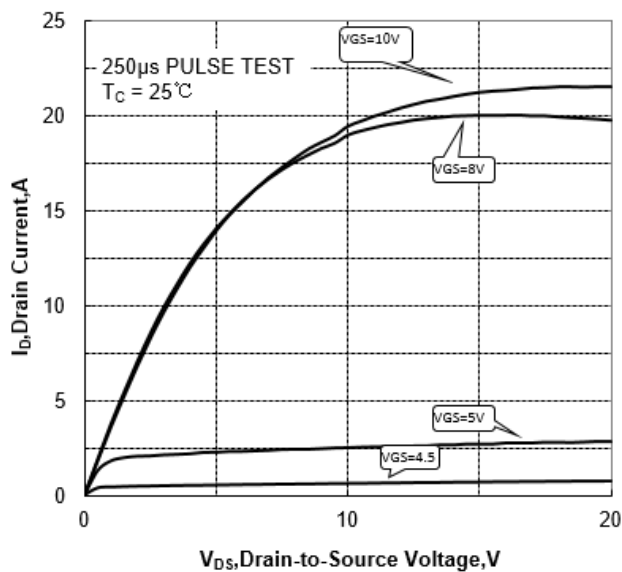


Figure 5 Typical Transfer Characteristics

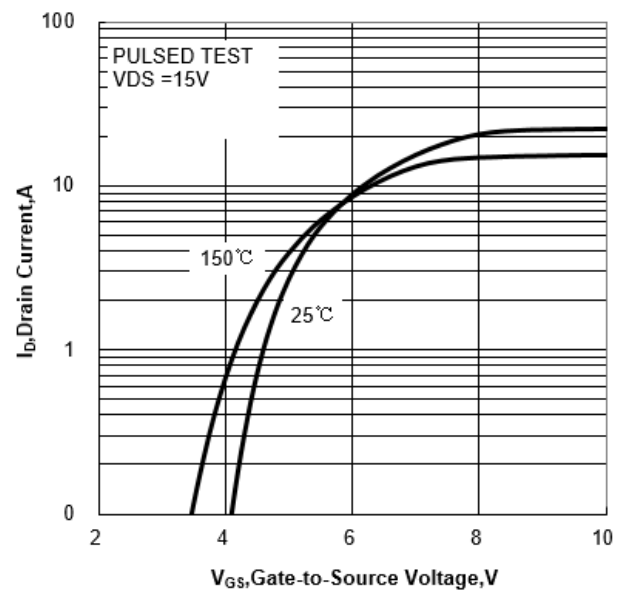


Figure 6 Typical Drain to Source ON Resistance vs Drain Current

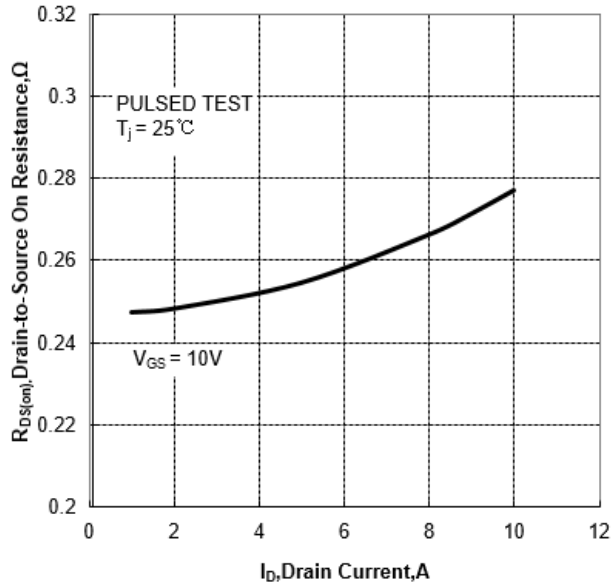


Figure 7 Typical Drain to Source on Resistance vs Junction Temperature

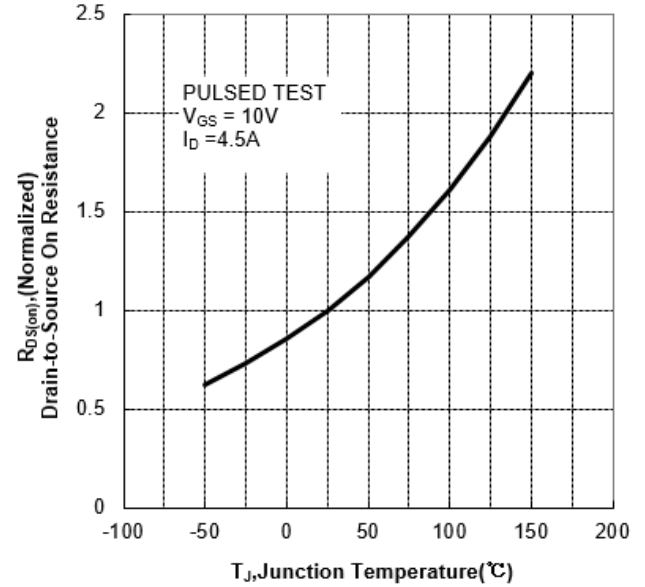


Figure 8 Typical Threshold Voltage vs Junction Temperature

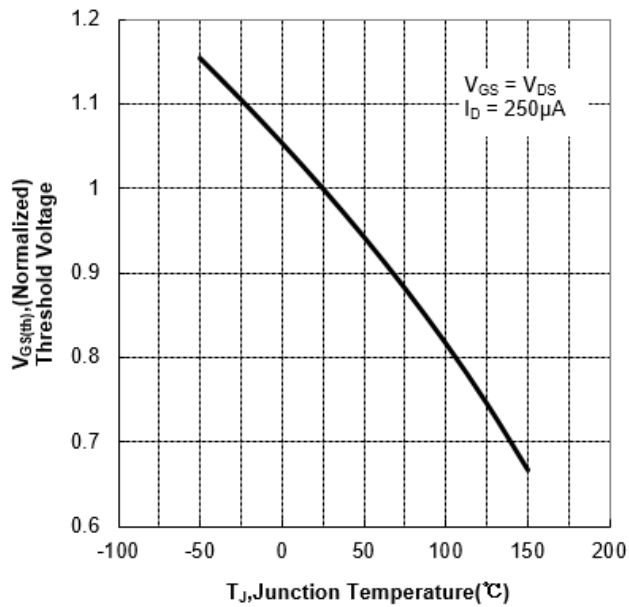


Figure 9 Typical Breakdown Voltage vs Junction Temperature

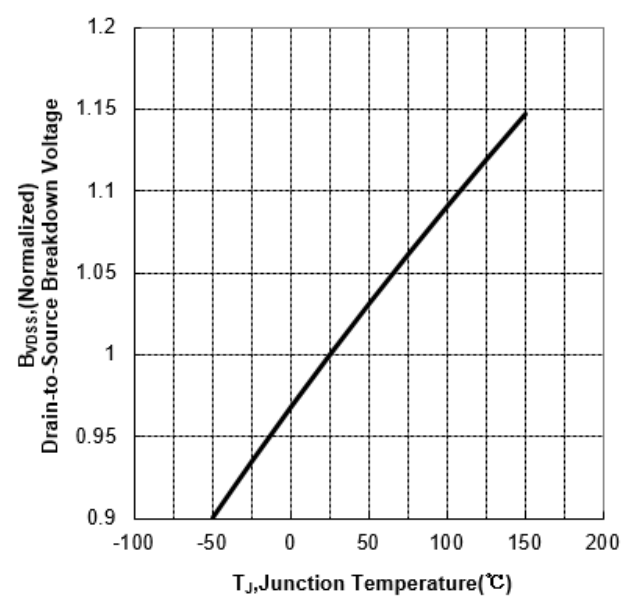


Figure 10 Typical Theshold Voltage vs Junction Temperature

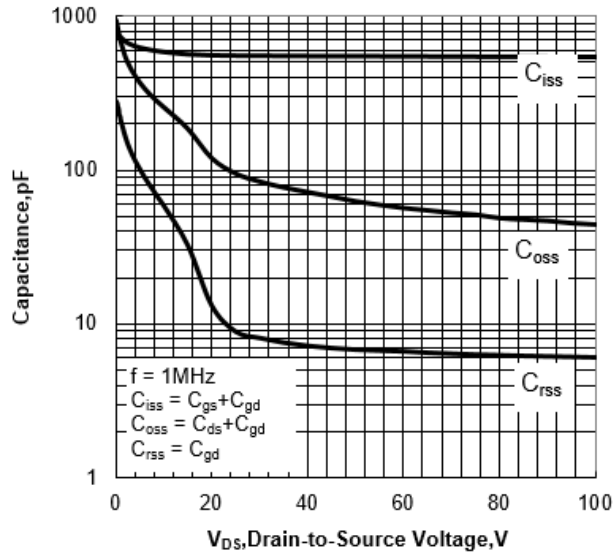
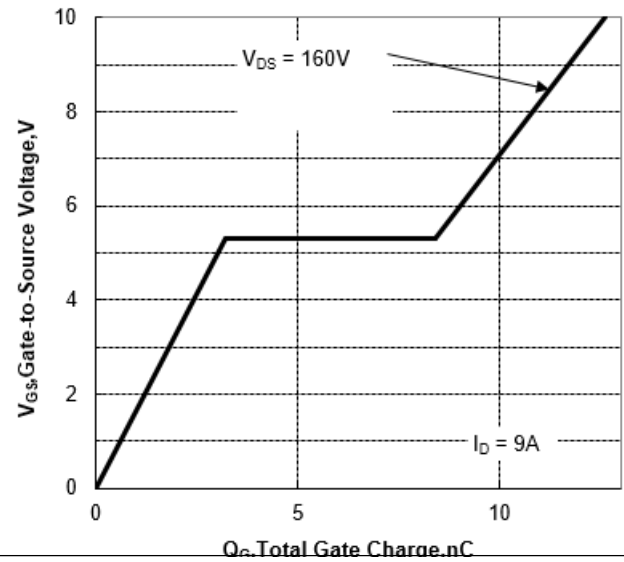


Figure 11 Typical Breakdown Voltage vs Junction Temperature



Test Circuit and Waveform

Figure 12 Gate Charge Test Circuit

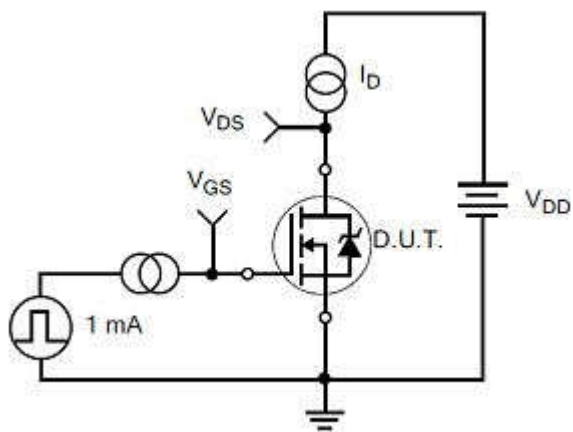


Figure 13 Gate Charge Waveforms

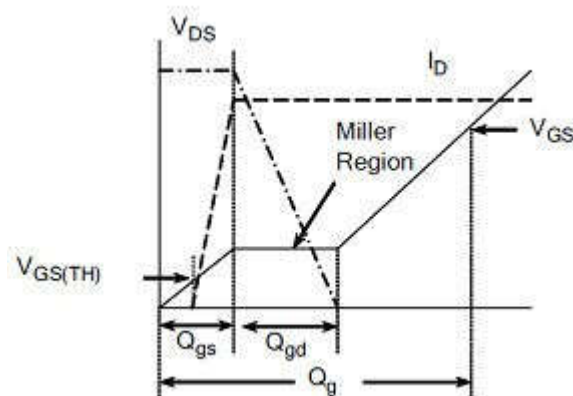


Figure 14 Resistive Switching Test Circuit

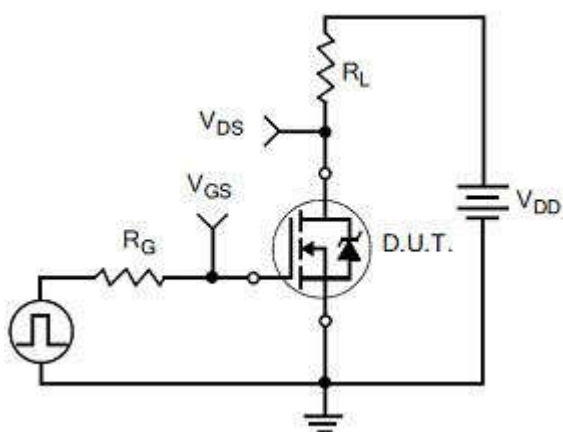


Figure 15 Resistive Switching Waveforms

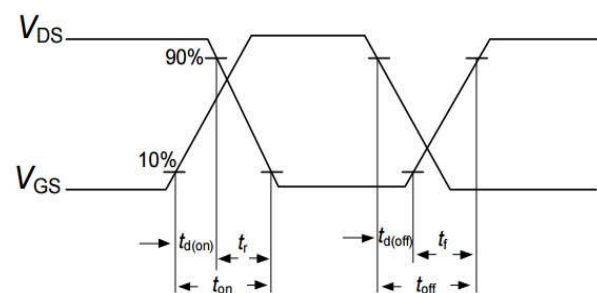


Figure 16 Diode Reverse Recovery Test Circuit

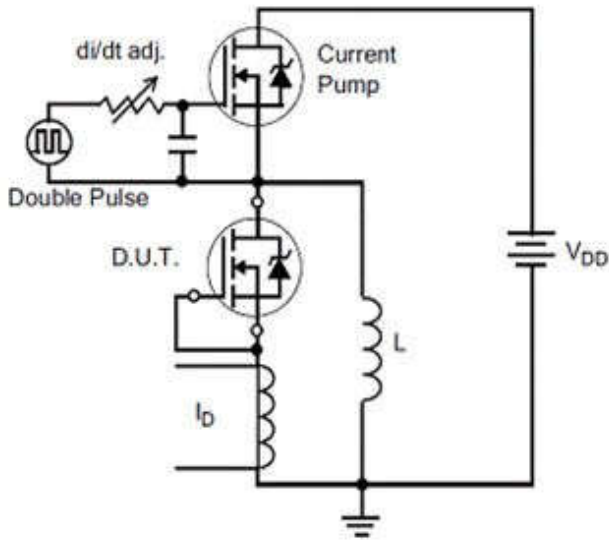


Figure 17 Diode Reverse Recovery Waveform

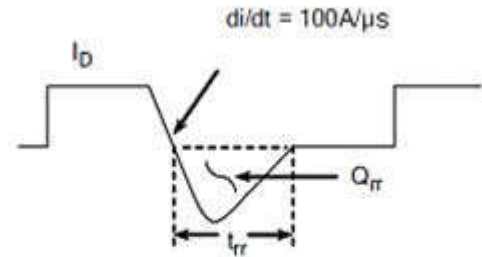


Figure 18 Unclamped Inductive Switching Test Circuit

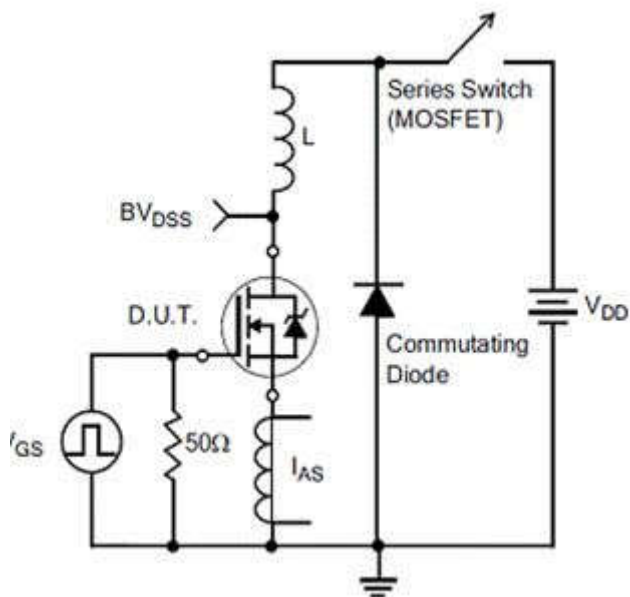
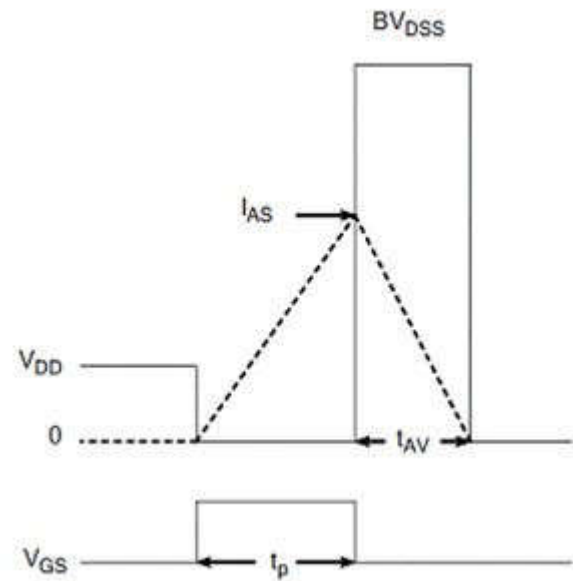
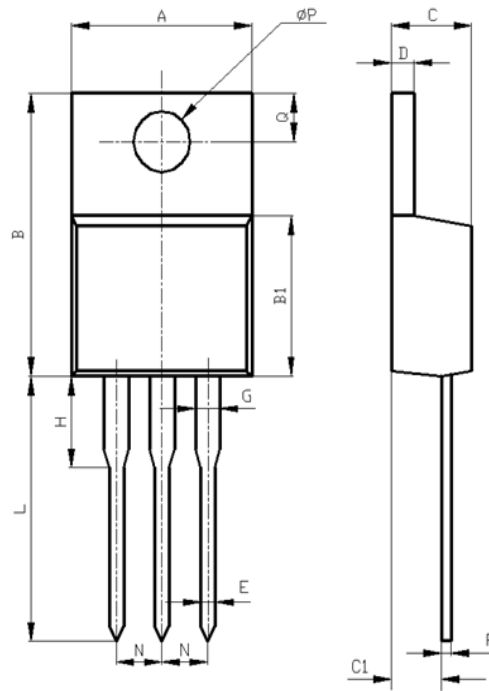


Figure 19 Unclamped Inductive Switching Waveform





Items	Values(mm)	
	MIN	MAX
A	9.60	10.6
B	15.0	16.0
B1	8.90	9.50
C	4.30	4.80
C1	2.30	3.10
D	1.20	1.40
E	0.70	0.90
F	0.30	0.60
G	1.17	1.37
H	2.70	3.80
L	12.6	14.8
N	2.34	2.74
Q	2.40	3.00
Ø P	3.50	3.90

TO-220 Package



迈诺斯科技

IRF630N

NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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